



### **AOWF10T60P Information**

Heisener.com

Part Number AOWF10T60P

Manufacturer Alpha & Omega Semiconductor Inc.

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 600V 10A TO-262

Package TO-262-3 Full Pack, I2Pak

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com



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## **Certified Quality**

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# **AOWF10T60P Specifications**

Manufacturer Part Number         AOWF10T60P           Manufacturer         Alpha & Omega Semiconductor Inc.           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-262-3 Full Pack, 12Pak           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         10A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         40nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1595pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         28W (Tc)           Rds On (Max) @ Id, Vgs         700 mOhm @ 5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-262F           Package / Case         TO-262F		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-262-3 Full Pack, I2Pak           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         10A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         40nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1595pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         28W (Tc)           Rds On (Max) @ Id, Vgs         700 mOhm @ 5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-262F	Manufacturer Part Number	AOWF10T60P
PackageTo-262-3 Full Pack, 12PakSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1595pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)28W (Tc)Rds On (Max) @ Id, Vgs700 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262F	Manufacturer	Alpha & Omega Semiconductor Inc.
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Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         10A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         40nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1595pF @ 100V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         28W (Tc)           Rds On (Max) @ Id, Vgs         700 mOhm @ 5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-262F		Transistors - FETs, MOSFETs - Single
FET Type  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  600V  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  5V @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Supplier Device Package  N-Channel  NO-Channel  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  10A  10V  10V  10V  10V  10V  10V  10V	Package	TO-262-3 Full Pack, I2Pak
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1595pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)28W (Tc)Rds On (Max) @ Id, Vgs700 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262F	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  10A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sv @ 250μA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  700 mOhm @ 5A, 10V  Operating Temperature  Supplier Device Package  600V  10A (Tc)  10A (T	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1595pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)28W (Tc)Rds On (Max) @ Id, Vgs700 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262F	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1595pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)28W (Tc)Rds On (Max) @ Id, Vgs700 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262F	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1595pF @ 100V  Vgs (Max)  ETH Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  5V @ 250μA  40nC @ 10V  1595pF @ 100V  28W (Tc)  28W (Tc)  700 mOhm @ 5A, 10V  -55°C ~ 150°C (TJ)  Through Hole	Current - Continuous Drain (Id) @ 25°C	10A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1595pF @ 100V  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  700 mOhm @ 5A, 10V  Operating Temperature  Supplier Device Package  40nC @ 10V  40nC @ 10V  1595pF @ 100V  1595pF @ 100V  28W (Tc)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Through Hole  Supplier Device Package  1595pF @ 100V  ±30V	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)28W (Tc)Rds On (Max) @ Id, Vgs700 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262F	Gate Charge (Qg) (Max) @ Vgs	40nC @ 10V
FET Feature -  Power Dissipation (Max) 28W (Tc)  Rds On (Max) @ Id, Vgs 700 mOhm @ 5A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-262F	Input Capacitance (Ciss) (Max) @ Vds	1595pF @ 100V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  700 mOhm @ 5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-262F	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs700 mOhm @ 5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-262F	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-262F	Power Dissipation (Max)	28W (Tc)
Mounting TypeThrough HoleSupplier Device PackageTO-262F	Rds On (Max) @ Id, Vgs	700 mOhm @ 5A, 10V
Supplier Device Package TO-262F	Operating Temperature	-55°C ~ 150°C (TJ)
	Mounting Type	Through Hole
Package / Case TO-262-3 Full Pack, I2Pak	Supplier Device Package	TO-262F
	Package / Case	TO-262-3 Full Pack, I2Pak
Report errors?		Report errors?

#### **AOWF10T60P Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **AOWF10T60P Payment Methods**





















### **AOWF10T60P Shipping Methods**













If you have any question about AOWF10T60P, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com